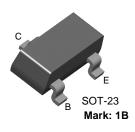


SEMICONDUCTOR®

MMBT2222

NPN General Purpose Amplifier

• Sourced from process 19.



Absolute Maximum Ratings* $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
√ _{CEO}	Collector-Emitter Voltage	30	V
√ _{CBO}	Collector-Base Voltage	60	V
√ _{EBO}	Emitter-Base Voltage	5.0	V
c	Collector Current - Continuous	0.6	A
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These rating are based on a maximum junction temperature of 150 degrees C.
2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	30		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10\mu {\rm A}, I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu A, I_{\rm C} = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		10	μΑ
		$V_{CB} = 50V, I_E = 0, T_a = 125^{\circ}C$		10	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		10	nA
On Charac	teristics				
h _{FE}	DC Current Gain	I _C = 0.1mA, V _{CE} = 10V	35		
		I _C = 1.0mA, V _{CE} = 10V	50		
		I _C = 10mA, V _{CE} = 10V	75		
		$I_{C} = 150 \text{mA}, V_{CE} = 10 \text{V}^{*}$	100	300	
		$I_{C} = 150 \text{mA}, V_{CF} = 1.0 \text{V}^{*}$	50		
		$I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}^{*}$	30		
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 150mA, I _B = 15V		0.4	V
- ()		$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm V}$		1.6	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150mA, I _B = 15V		1.3	V
. /		I _C = 500mA, I _B = 50V		2.6	

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Electrical Characteristics (Continued) T_a=25°C unless otherwise noted Symbol Parameter **Test Condition** Min. Max. Units **Small Signal Characteristics** Curent Gain Bandwidth Product $\mathsf{I}_{\mathsf{C}} = 20\mathsf{m}\mathsf{A},\,\mathsf{V}_{\mathsf{C}\mathsf{E}} = 20\mathsf{V},\,\mathsf{f} = 100\mathsf{M}\mathsf{Hz}$ 250 f_{T} $V_{CB} = 10V, I_E = 0, f = 1MHz$ **Output Capacitance** 8.0 pF C_{obo} $V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$ Input Capacitance 30 pF C_{ibo} **Switching Characteristics** $V_{CC} = 30V, V_{BE(OFF)} = 0.5V, I_{C} = 150mA, I_{B1} = 15mA$ Delay Time 10 ns td **Rise Time** 25 t_r ns $V_{CC} = 30V, I_C = 150mA,$ 225 t_s Storage Time ns $I_{B1} = I_{B2} = 15 \text{mA}$ Fall Time 60 ns t_f

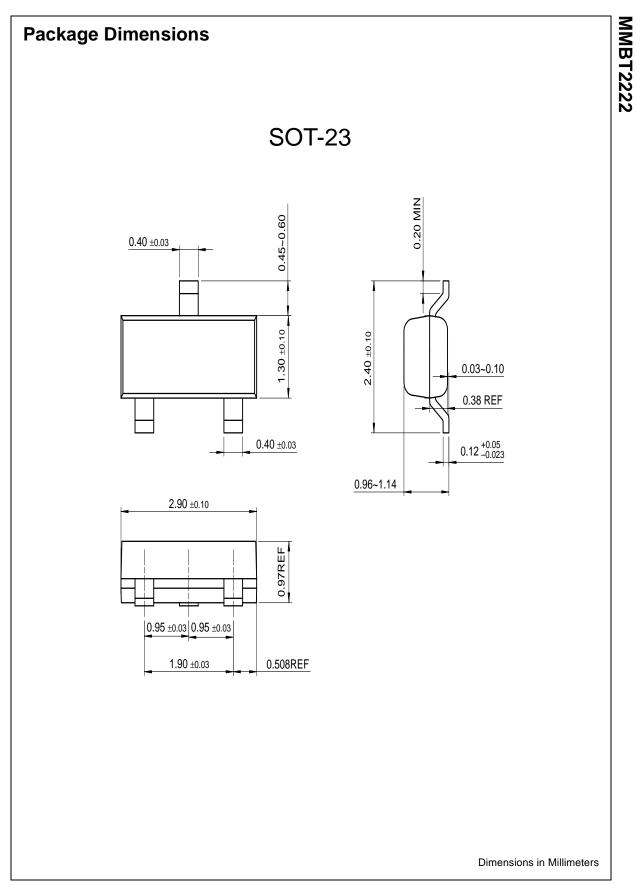
* Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%

Thermal Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

* Device mounted on FR-4PCB 1.6" \times 1.6" \times 0.06".

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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